



ELECTRONIC TUBE REFERENCE

3HT6

Voltage Pentode - Remote Cutoff (single) electronic tube

CONSOLIDATED TECHNICAL DATA

1 SECTION

CONSTRUCTION

PENTODE

Semi-remote-cutoff pentode designed for AGC-controlled television IF amplifier stages. Its gradual cutoff characteristic provides useful gain regulation while handling wideband television intermediate-frequency signals.

GENERAL CHARACTERISTICS

BASE DESIGNATION	—	BASE PINS	9
NOMINAL HEATER	3.15 V / 600 mA	PARALLEL HEATER	— / —
HEATING	Indirect	SERIES OPERATION	Not specified
CATHODE ARRANGEMENT	Separate cathodes	SECTION CONSTRUCTION	Similar

SECTION RATINGS

SECTION 1 Pentode	
PLATE RESISTANCE	143000 Ω
TRANSCONDUCTANCE	0.014 S
MAXIMUM PLATE VOLTAGE	300 V
MAXIMUM SCREEN VOLTAGE	300 V
MAXIMUM PLATE DISSIPATION	2.5 W
MAXIMUM SCREEN DISSIPATION	0.55 W
MAXIMUM CATHODE CURRENT	25 mA
MAXIMUM HEATER-CATHODE VOLTAGE	200 V
WARM-UP TIME	11 s
Published promoted fields populated by semantic headings; identical repeated sections compressed.	

Semi-remote-cutoff pentode for AGC-controlled television IF amplifier stages.

SOURCE OPERATING CONDITIONS

1965 Sylvania Electronic Tubes Vol3

Published test conditions and operating points. Values on this page are preserved as reported by this source.

1965 SYLVANIA ELECTRONIC TUBES VOL3

Section 1 · Pentode

OTHER		
PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
Plate voltage	125 V	—
Screen-grid voltage	125 V	—
Cathode bias resistor	56 Ohm	—
Plate current	15 mA	—
Screen-grid current	4 mA	—

CHARACTERISTICS		
PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
Plate resistance	143000 Ohm	—
Transconductance	14000 uS	—

CAPACITANCE		
PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
Grid-to-plate capacitance	0.024 pF	Shielded
Input capacitance	8.7 pF	Shielded
Output capacitance	3 pF	Shielded

SOURCE OPERATING CONDITIONS

SOURCE PDF

1966 Tung Sol Electronic Tubes 1 of 4

Published test conditions and operating points. Values on this page are preserved as reported by this source.

1966 TUNG SOL ELECTRONIC TUBES 1 OF 4

Section 1 · Pentode

OTHER		
PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
Plate voltage	125 V	IFAmplifier
Screen voltage	125 V	IFAmplifier
Cathode-bias resistor	56 Ω	IFAmplifier
Plate current	15 mA	IFAmplifier
Screen current	4 mA	IFAmplifier

CHARACTERISTIC		
PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
Transconductance	14000 μS	Section1
Plate resistance	0.143 M Ω	Section1
Grid-1 cutoff bias at 50 μS	-6.7 V	Section1
Transconductance at -1.5 V	12000 μS	Section1
Transconductance at -3.6 V	300 μS	Section1
Hot input resistance at 44 MHz	12700 Ω	Section1

CAPACITANCE		
PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
Hot input capacitance at 44 MHz	7.45 pF	Section1